AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning at page 2, line 24, with the following rewritten paragraph:

When an ultrathin conductive film is measured, an eddy current produced inside of a substrate such as a semiconductor wafer is not negligible. Accordingly, in order to measure the film thickness of the ultrathin conductive film, influence from the interior of the substrate should be considered as a measurement environment which would adversely affect measurement with the eddy current sensor. Thus, complicated and troublesome processes are required to measure the film thickness of the substrate.

Please replace the paragraph beginning at page 3, line 1, with the following rewritten paragraph:

Disclosure-Summary of Invention

Please replace the paragraph beginning at page 11, line 3, with the following rewritten paragraph:

Best Mode for Carrying Out the Invention Detailed Description of Preferred Embodiments

Please replace the paragraph beginning at page 34, line 21, with the following rewritten paragraph:

Further, the eddy current sensor may be used for polishing prediction or preventive maintenance. For example, the impedance properties of the eddy current sensor which are obtained from a wafer being polished are measured every predetermined time. Based on a correlation between the impedance properties and model data, polishing prediction is performed so as to predict a remaining time required to obtain the impedance properties corresponding to the model data of the endpoint of the polishing process. Thus, irrespective of rotation of the polishing table in the CMP apparatus, it is possible to detect a polishing endpoint at intervals shorter than a period of time required to make one revolution of the polishing table. Further, it is possible to predict a remaining time until the polishing endpoint at an early stage. Accordingly,

since the progress of the polishing process can be checked, it is possible to promptly cope with an anomaly caused during polishing.